Amendments to the Claims:

The following listing of claims replaces all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device having ~~which has~~ a synthetic high-molecular compound, wherein the synthetic high-molecular compound covers ~~with which~~ a semiconductor element and at least part of electrical connecting means used for electrically connecting the semiconductor device to external devices; and ~~are covered, in which~~

the synthetic high-molecular compound contains a compound having a three-dimensional steric structure ~~which is~~ formed by linking plural third organosilicon polymers, wherein each of the third organosilicon polymers ~~each of which~~ has a molecular weight of 2×10^4 to 8×10^5 and is ~~which have been~~ formed by linking a ~~at least one~~ first organosilicon ~~polymers~~ polymer having a crosslinked structure using siloxane (Si-O-Si combination) with a ~~at least one~~ second organosilicon ~~polymers~~ polymer having a linear linked structure using siloxane through siloxane bonds, with covalent bonds resulting from an addition reaction,

wherein the molecular weight of the first organosilicon polymer is lower than that of the second organosilicon polymer.

2. (Currently Amended) The semiconductor device as claimed in claim 1, wherein each of the ~~in which the synthetic high-molecular compound contains a compound having a three-dimensional steric structure which is formed by linking plural~~ third organosilicon polymers is, ~~each of which has a molecular weight of 2×10^4 to 8×10^5 and which have been~~ formed by alternately and linearly linking a first organosilicon polymer having a crosslinked structure using siloxane with a second organosilicon polymer having a linear linked structure

using siloxane through a siloxane bond, with covalent bonds resulting from an addition reaction.

3. (Currently Amended) The semiconductor device as claimed in claim 1, wherein ~~in which~~

the semiconductor element is selected from the group consisting of ~~either~~ a SiC semiconductor element using a wide gap semiconductor and ~~or~~ a GaN semiconductor element using a wide gap semiconductor,

the first organosilicon polymer is ~~at least one~~ selected from the group consisting of polyphenylsilsesquioxane, polymethylsilsesquioxane, polyethylsilsesquioxane, ~~and~~ polypropylsilsesquioxane, and combinations thereof; and

the second organosilicon polymer is ~~at least one~~ selected from the group consisting of polydimethylsiloxane, polydiethylsiloxane, polydiphenylsiloxane, ~~and~~ polymethylphenylsiloxane, and combinations thereof.

4. (Currently Amended) The semiconductor device as claimed in claim 1, wherein ~~in which~~

the semiconductor element is selected from the group consisting of a wide gap semiconductor light-receiving element, a wide gap semiconductor light-emitting element, and ~~or~~ a combination thereof,

the first organosilicon polymer is ~~at least one~~ selected from the group consisting of polyphenylsilsesquioxane, polymethylsilsesquioxane, polyethylsilsesquioxane, ~~and~~ polypropylsilsesquioxane, and combinations thereof; and

the second organosilicon polymer is ~~at least one~~ selected from the group consisting of polydimethylsiloxane, polydiethylsiloxane, polydiphenylsiloxane, ~~and~~ polymethylphenylsiloxane, and combinations thereof.

5-15. (Canceled)